

Features

- InGaAs/InP PIN Photodiode
- High responsivity at 1310nm and 1550nm
- Low dark current
- Fast response
- Operate at -40~85 °C
- Active diameter is 20 μ m

Applications

- 10G Optical Receiver
- Data and Telecommunication

Absolute Maximum Ratings(Tc=25°C)

Parameter	Symbol	Value	Unit
Supply Reverse voltage	V_R	20	V
Forward Current	I_F	2	mA
Reverse Current	I_R	1	mA
Operating Temperature	T_{opr}	-40~+85	°C
Storage Temperature	T_{stg}	-40~+85	°C

Optical and Electrical Characteristics(Tc=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Active Area (Dia.)			20		μ m	-
Detection Range		1100	1310	1650	nm	-
Responsivity	R	0.75	0.8	-	A/W	$V_R=5V, \lambda=1310nm$
Dark Current	I_{dark}		1	2	nA	$V_R=5V$
Capacitance	C		0.2	0.25	pF	$V_R=5V$
Bandwidth	BW	10	14		GHz	$V_R=5V, R_L=50\Omega$

Chip dimensions

